



- L31: (2464) single near2 anchor \$4
- L32: (36) 17 near5 31
- L33: (2) "6551816".pn
- L34: (1) Forward citation search 1
- L35: (4) Backward citation search 1
- L36: (5) 29 33
- L37: (1) Forward citation search 2
- L38: (4) Backward citation search 2
- L39: (1) Forward citation search 3
- L40: (5) Backward citation search 3
- L41: (1) Forward citation search 4
- L42: (7) Backward citation search 4
- L43: (0) Forward citation search 5
- L44: (4) Backward citation search 5
- L45: (1) Forward citation search 6
- L46: (6) Backward citation search 6
- L47: (2) Forward citation search 7
- L48: (2) Forward citation search 8
- L49: (4886) (257/700,703,758).CCLS.
- L50: (1) 31 and 49
- L51: (197) 49 and 18
- L52: (4) 51 and 28
- L53: (4973) 28 and 17
- L54: (1236) 28 same 17
- L55: (57) 54 and 48

DBs: US-PGPUB, USPAT, EPO, JPO, DERWENT, IBM, TDB

☐ Plurals

Default operator: OR

☐ Highlight all hit terms initially

Dec 2004

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BRS form IS&B form Image Text HTML

	U	Inventor	Document#	Issue	P	Title	Current	Current X	Retrieval	S	C	P	Image	Doc	P
1	<input type="checkbox"/>	Palmer, Willi	US 2004020	2004:1	1	Through-via vertical interconnects, through-v	257/700:257/698			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200402	<input type="checkbox"/>
2	<input type="checkbox"/>	Meguro, Hise	US 2004014	20040:2		Semiconductor memory device	257/776:257/752;			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200401	<input type="checkbox"/>
3	<input type="checkbox"/>	Matsunaga,	US 2004013	20040:1		Semiconductor device and its manufacturing	257/758;			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200401	<input type="checkbox"/>
4	<input type="checkbox"/>	Fukuda, Yuta	US 2004008	20040:1		Semiconductor equipment	257/758:257/E23.01			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200400	<input type="checkbox"/>
5	<input type="checkbox"/>	Teh, Young-	US 2004006	20040:1		Novel copper metal structure for the reducti	257/751:257/758;			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200400	<input type="checkbox"/>
6	<input type="checkbox"/>	Arafani, Kats	US 2003023	20031:4		Memory device and method of production an	257/758:257/E27.00;			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200302	<input type="checkbox"/>
7	<input type="checkbox"/>	Saitoh, Yumi	US 2003020	20031:1		METHOD OF FORMING A MULTI-LAYERED W	257/758:257/E23.14			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200302	<input type="checkbox"/>
8	<input type="checkbox"/>	Dennison, Ch	US 2003008	20030:1		Semiconductor processing methods of formin	257/758:257/774;			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200300	<input type="checkbox"/>
9	<input type="checkbox"/>	Cho, Tai-Hwei	US 2002018	20021:1		Semiconductor device having multilevel inter	257/758:257/E23.14			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200201	<input type="checkbox"/>
10	<input type="checkbox"/>	Teh, Young-	US 2002017	20021:1		Novel copper metal structure for the reducti	257/751:257/700;			<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 200201	<input type="checkbox"/>

/ Hits Details HTML

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